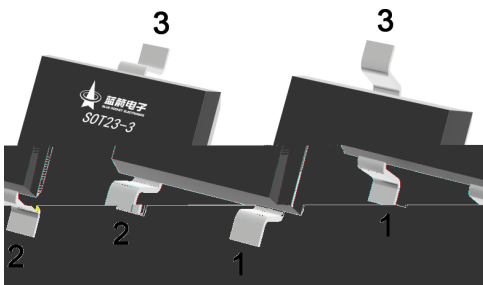
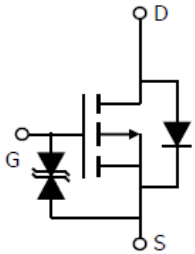


SOT23-3 P MOS
P- CHANNEL MOSFET in a SOT23-3 Plastic Package.

$V_{DS} (V) = -20V$ $I_D = -5.0A (V_{GS} = \pm 10V)$
 $R_{DS(ON)} < 40 m\Omega, V_{GS} = -4.5V$
 $R_{DS(ON)} < 53 m\Omega, V_{GS} = -2.5V$
 HF Product.

Load switch Battery protection.



PIN 1 G PIN 2 S PIN 3 D

Marking	AFH
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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-5.0	A
Drain Current-Pulsed	I_{DM}	-16	A
Maximum Power Dissipation	P_D	1.5	W
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to +150	$^{\circ}C$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	83.3	$^{\circ}C/W$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$B_{V_{DSS}}$	$V_{GS}=0V$ $I_{DS}=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V$ $V_{GS}=0V$			-1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 10V$ $V_{DS}=0V$			± 10	μA
Gate Threshold Voltage	V_{TH}	$V_{DS}=V_{GS}$ $I_{DS}=-250\mu A$	-0.3	-0.6	-0.9	V
Drain-Source On-State Resistance	R_{DS}	$V_{GS}=-4.5V$ $I_{DS}=-4A$		35	40	$m\Omega$
		$V_{GS}=-2.5V$ $I_{DS}=-4A$		45	53	
Input Capacitance	C_{iss}	$V_{DS}=-10V$ $V_{GS}=0V$ $f=1MHz$		935		pF
Output Capacitance	C_{oss}			92		
Reverse Transfer Capacitance	C_{rss}			83		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-10V$ $V_{GS}=-4.5V$ $R_G=3\Omega$ $R_L=2.2\Omega$		12		ns
Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			82		
Fall Time	t_f			35		
Total Gate Charge	Q_g	$V_{DS}=-10V$ $I_{DS}=-5.0A$ $V_{GS}=-4.5V$		8.5		nC
Gate to Source Gate Charge	Q_{gs}			1		
Gate to Drain "Miller" Charge	Q_{gd}			2.5		
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_{DS}=-1A$			-1.2	V

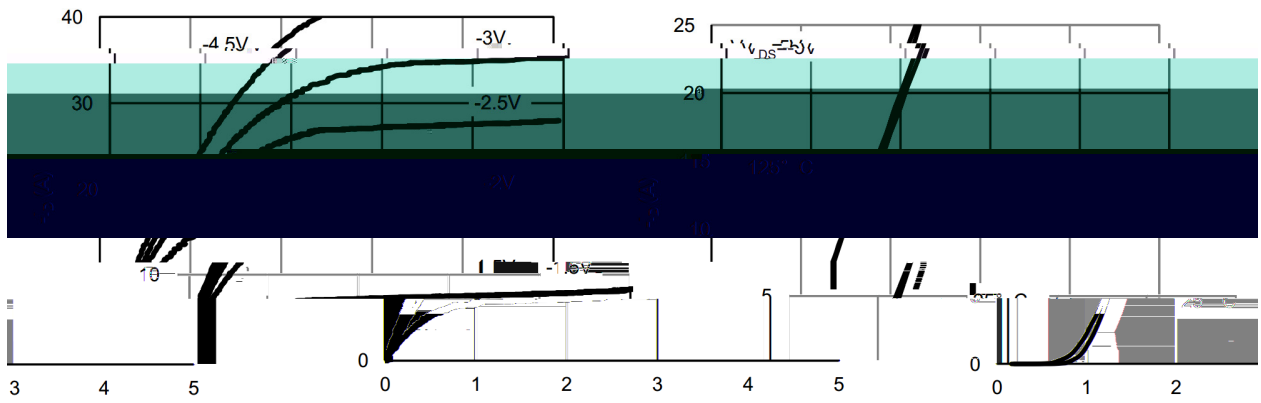


Figure 1: On-Resistance Characteristics

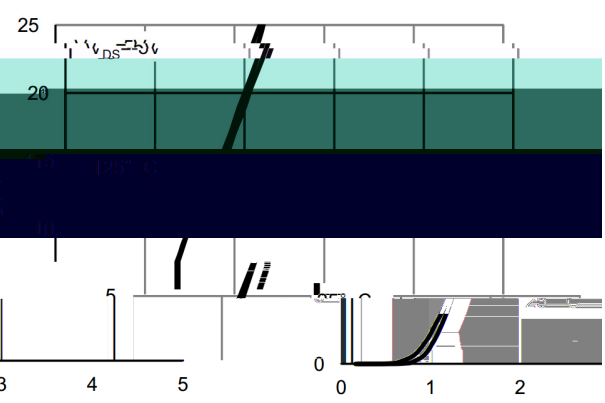


Figure 2: Transfer Characteristics

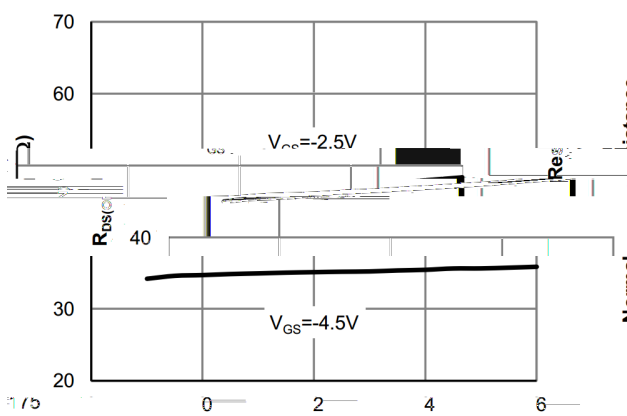


Figure 3: On-Resistance vs. Junction Temperature

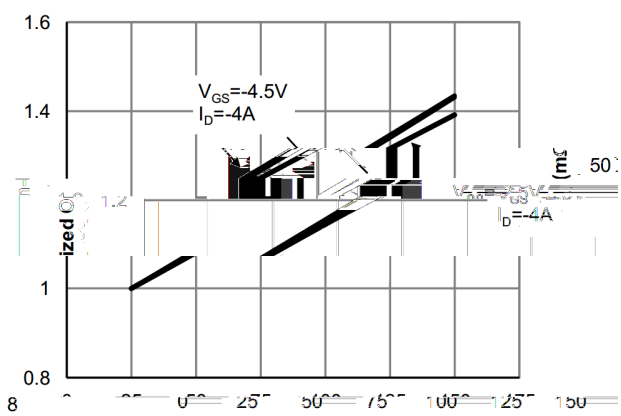


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

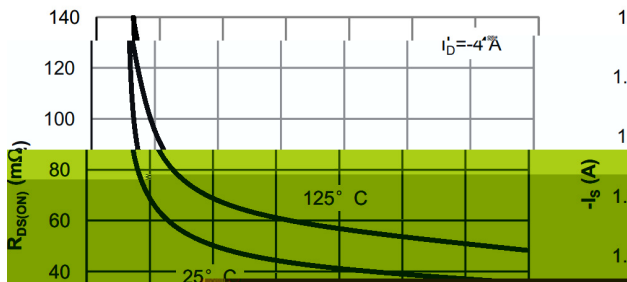


Figure 5: On-Resistance vs. Drain Current and Gate Voltage

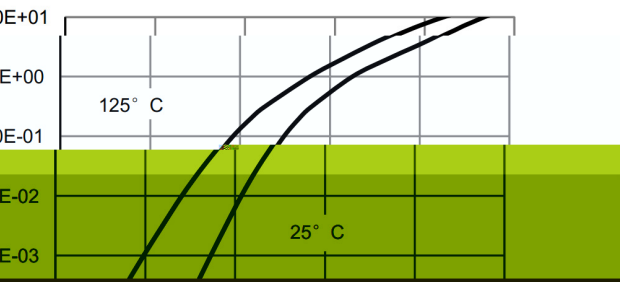


Figure 6: On-Resistance vs. Drain Current and Gate Voltage

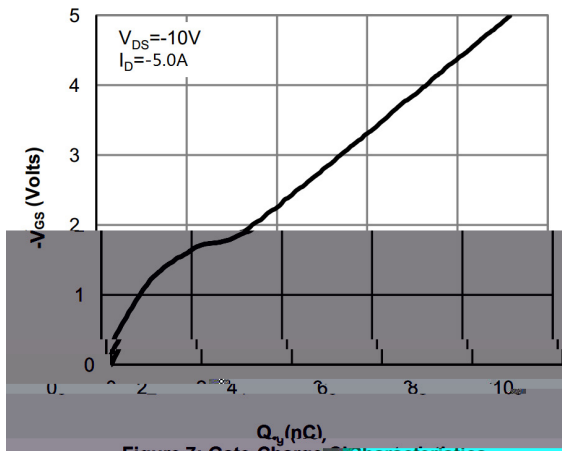


Figure 7. Q_g vs V_{gs} Characteristics

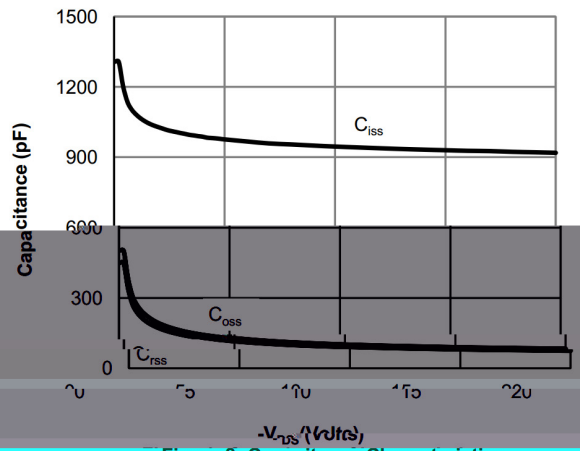


Figure 8. Capacitance vs V_{ds} Characteristics

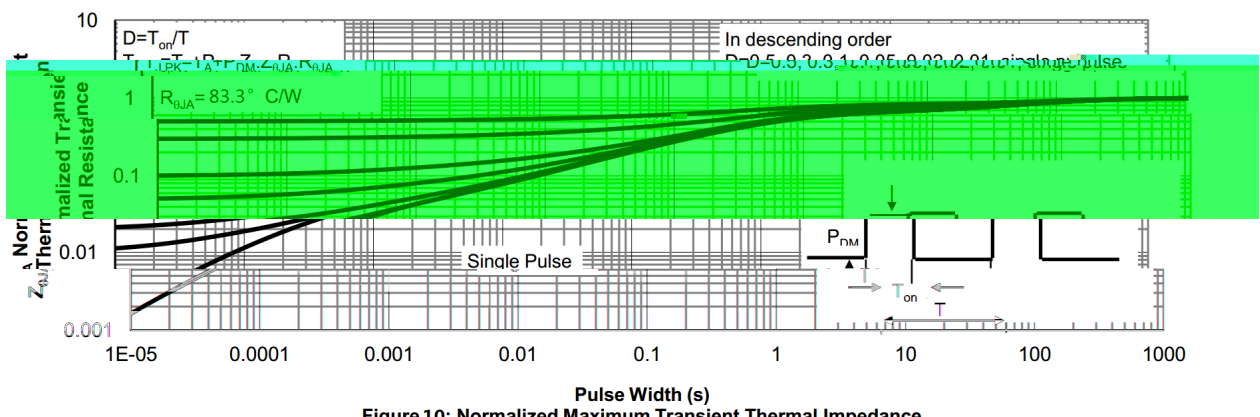
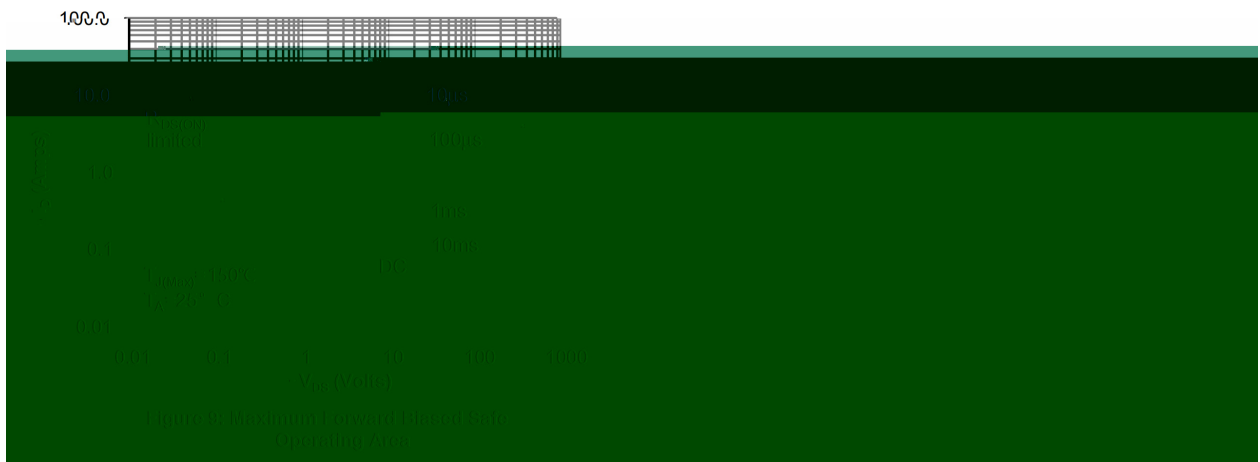
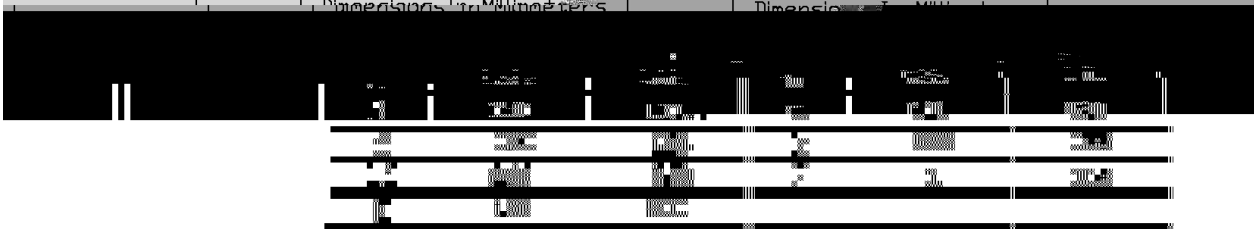
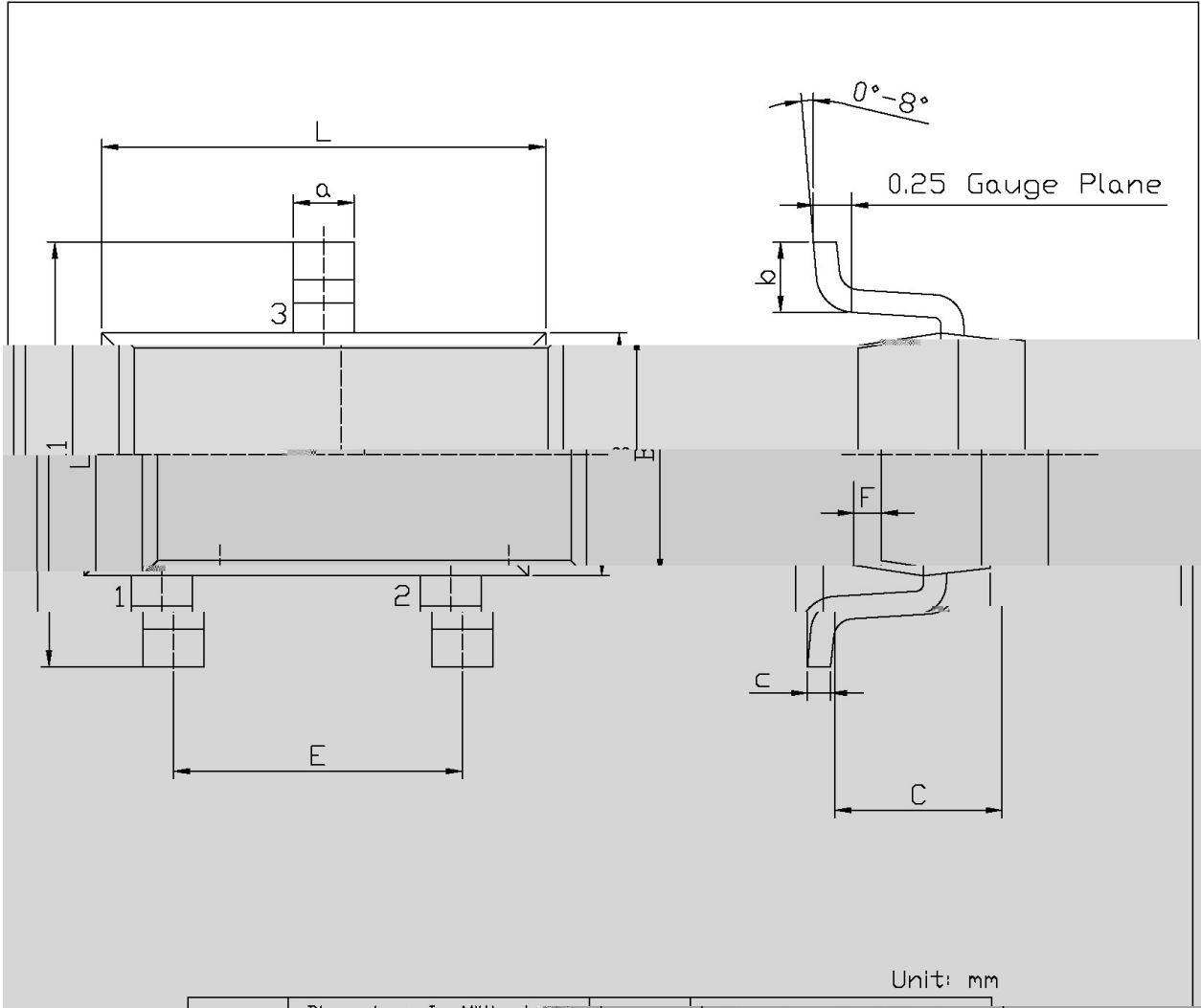
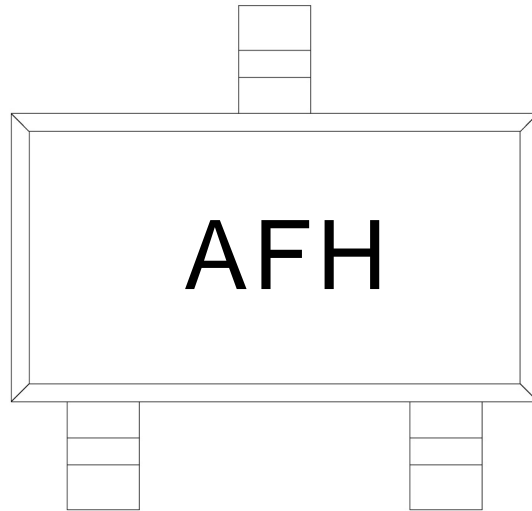


Figure 10. Normalized Maximum Transient Thermal Impedance



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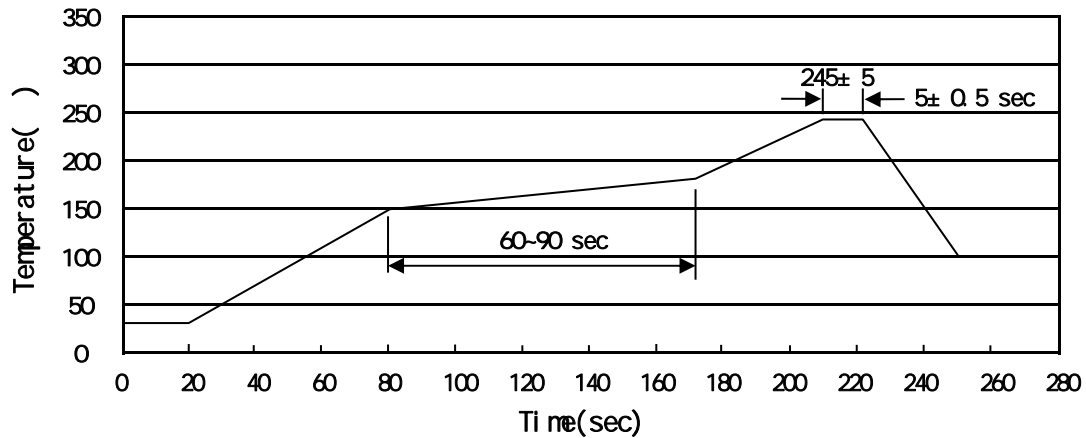
H:

AF:

Note:

H: Company Code

AF Product Type Code

Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-------|-----|-------|--------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5 | sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 x8	210x205x205	445x435x230